



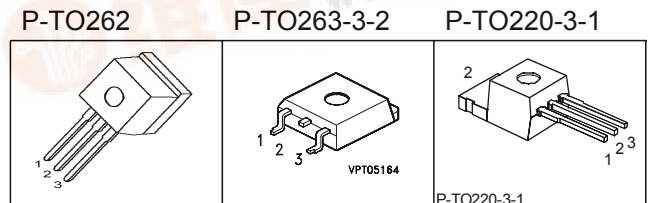
**SPP11N60S5, SPB11N60S5
SPI11N60S5**

Cool MOS™ Power Transistor

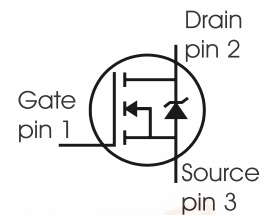
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

V_{DS}	600	V
$R_{DS(on)}$	0.38	Ω
I_D	11	A



Type	Package	Ordering Code	Marking
SPP11N60S5	P-TO220-3-1	Q67040-S4198	11N60S5
SPB11N60S5	P-TO263-3-2	Q67040-S4199	11N60S5
SPI11N60S5	P-TO262	Q67040-S4338	11N60S5



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	I_D	11 7	A
Pulsed drain current, t_p limited by T_{jmax}	I_D puls	22	
Avalanche energy, single pulse $I_D = 5.5\text{ A}, V_{DD} = 50\text{ V}$	E_{AS}	340	mJ
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ $I_D = 11\text{ A}, V_{DD} = 50\text{ V}$	E_{AR}	0.6	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	11	A
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	P_{tot}	125	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$



Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}, I_D = 11 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$	dv/dt	20	V/ns

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾	R_{thJA}	-	-	62	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}, I_D=11\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=500\mu\text{A}, V_{GS}=V_{DS}$	3.5	4.5	5.5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}, V_{GS}=0\text{V},$ $T_j=25^\circ\text{C},$ $T_j=150^\circ\text{C}$	-	-	25 250	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}, V_{DS}=0\text{V}$	-	-	100	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=7\text{A},$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$	-	0.34 0.92	0.38 -	Ω
Gate input resistance	R_G	$f=1\text{MHz}, \text{open Drain}$	-	29	-	

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 7\text{A}$	-	6	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	1460	-	pF
Output capacitance	C_{oss}		-	610	-	
Reverse transfer capacitance	C_{rss}		-	21	-	
Effective output capacitance, ³⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$ to 480V	-	45	-	pF
Effective output capacitance, ⁴⁾ time related	$C_{o(tr)}$		-	85	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 11\text{A}$, $R_G = 6.8\Omega$	-	130	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{d(off)}$		-	150	225	
Fall time	t_f		-	20	30	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$	-	10.5	-	nC
Gate to drain charge	Q_{gd}		-	24	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$, $V_{GS} = 0$ to 10V	-	41.5	54	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 11\text{A}$	-	8	-	V

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

² Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

³ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

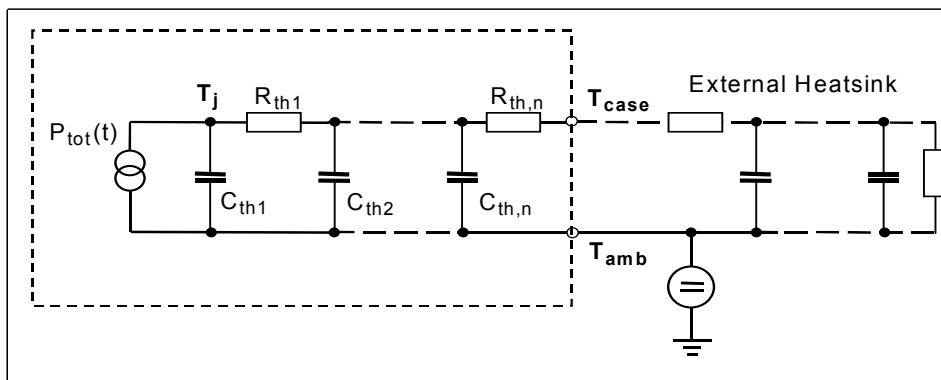
⁴ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^\circ\text{C}$	-	-	11	A
Inverse diode direct current, pulsed	I_{SM}		-	-	22	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=350\text{V}, I_F=I_S,$	-	650	1105	ns
Reverse recovery charge	Q_{rr}	$di_F/dt=100\text{A}/\mu\text{s}$	-	7.9	-	μC

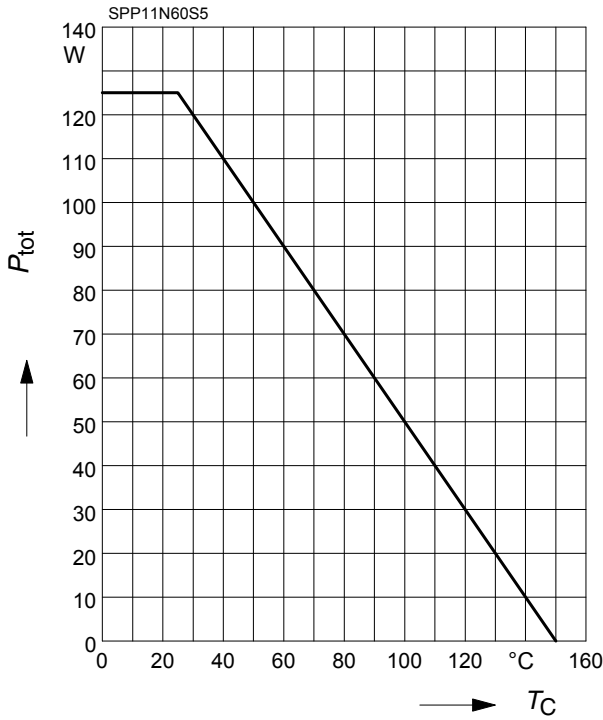
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.015	K/W	C_{th1}	0.0001878	Ws/K
R_{th2}	0.03		C_{th2}	0.0007106	
R_{th3}	0.056		C_{th3}	0.000988	
R_{th4}	0.197		C_{th4}	0.002791	
R_{th5}	0.216		C_{th5}	0.007285	
R_{th6}	0.083		C_{th6}	0.063	



1 Power dissipation

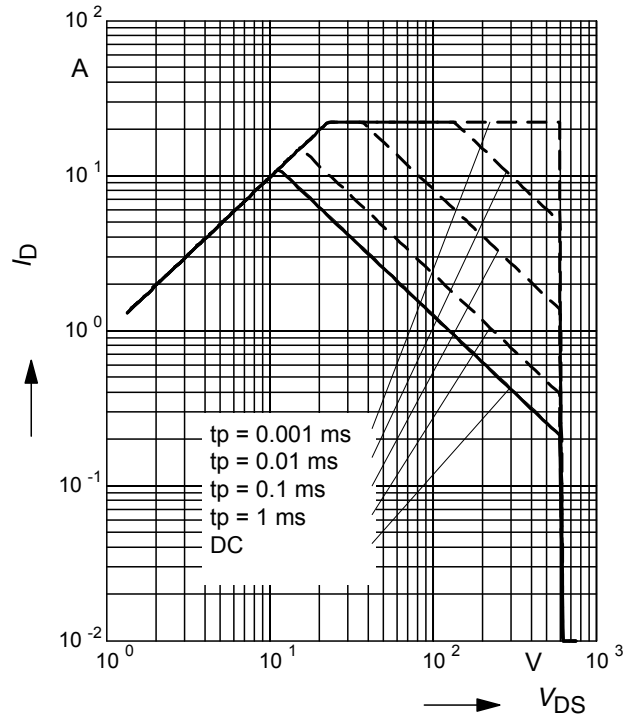
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

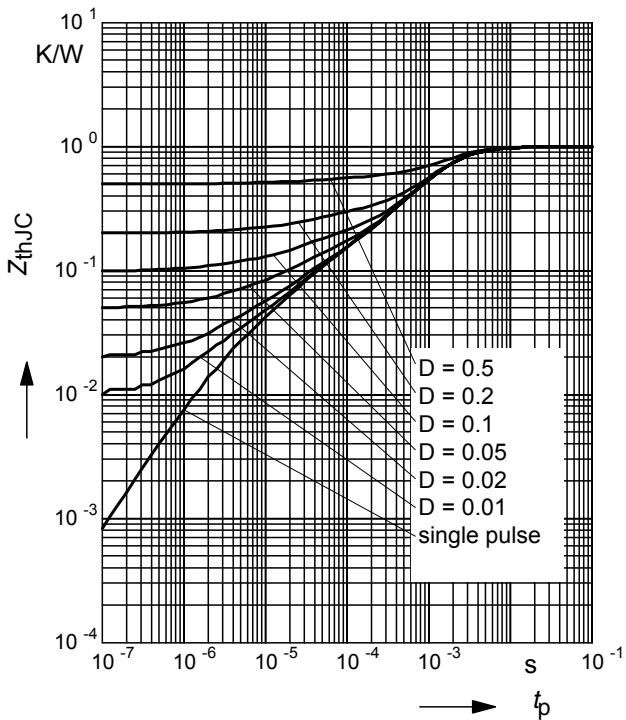
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$Z_{thJC} = f(t_p)$

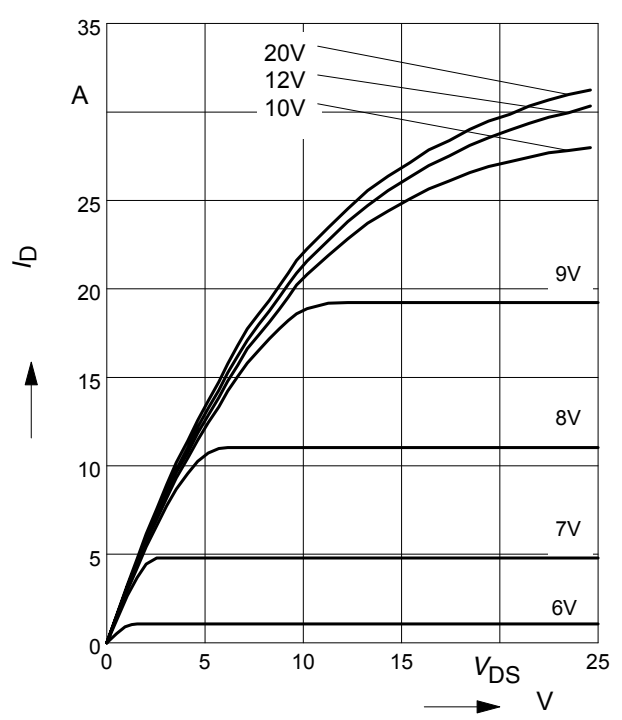
parameter: $D = t_p/T$



4 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

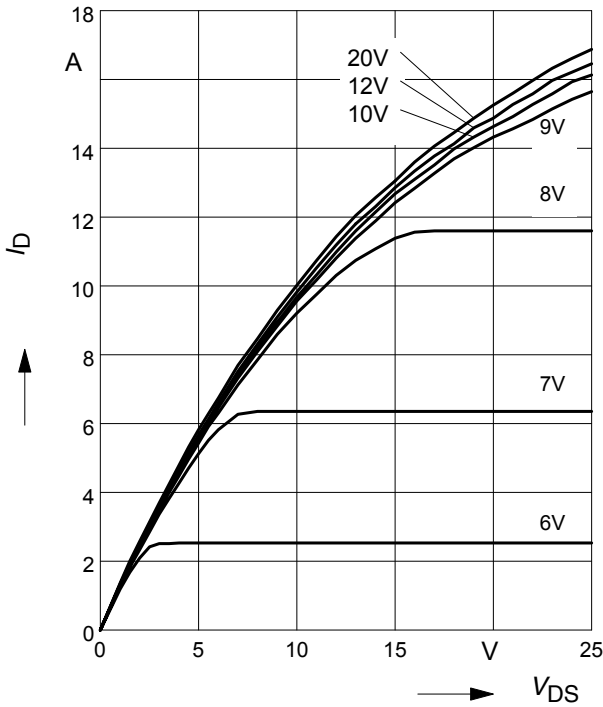
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

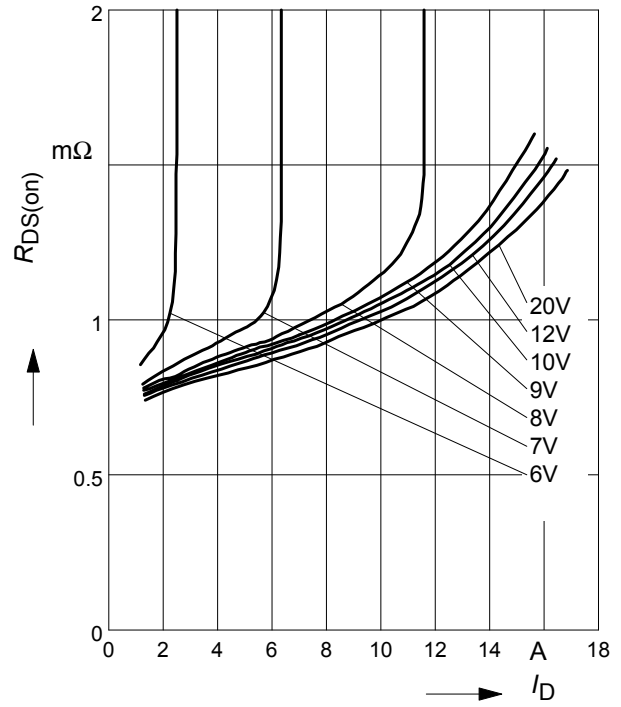
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

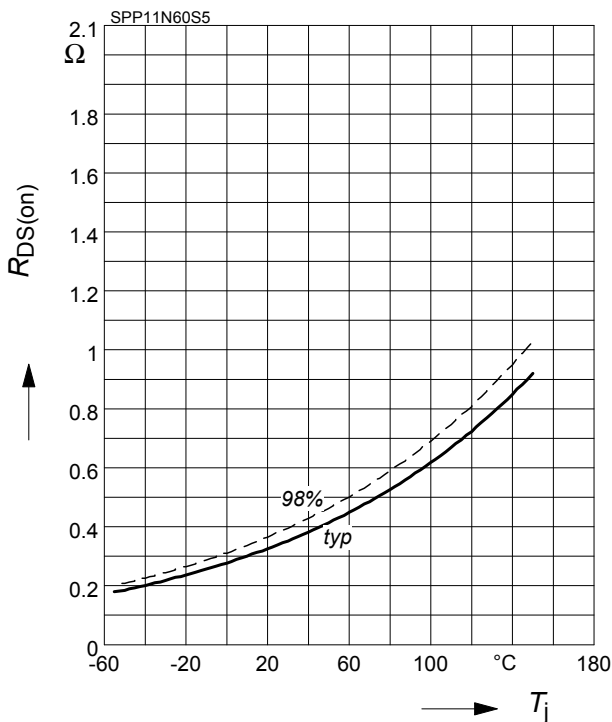
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



7 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

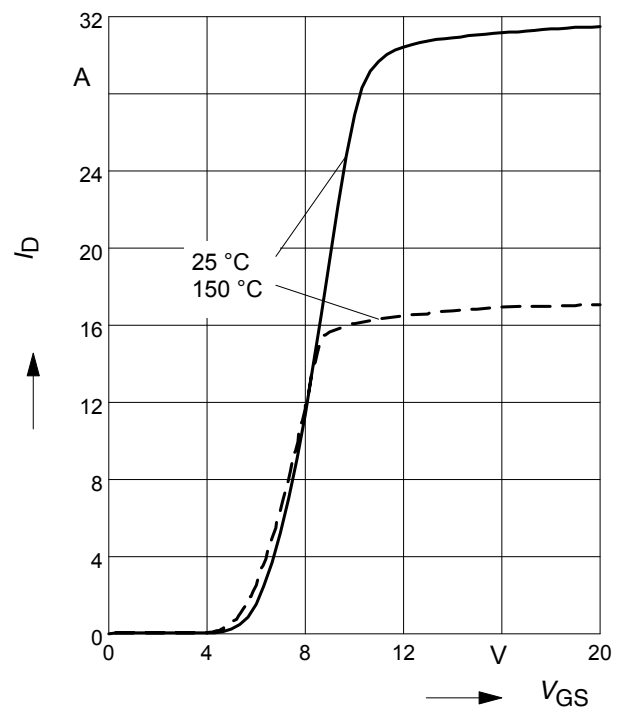
parameter: $I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

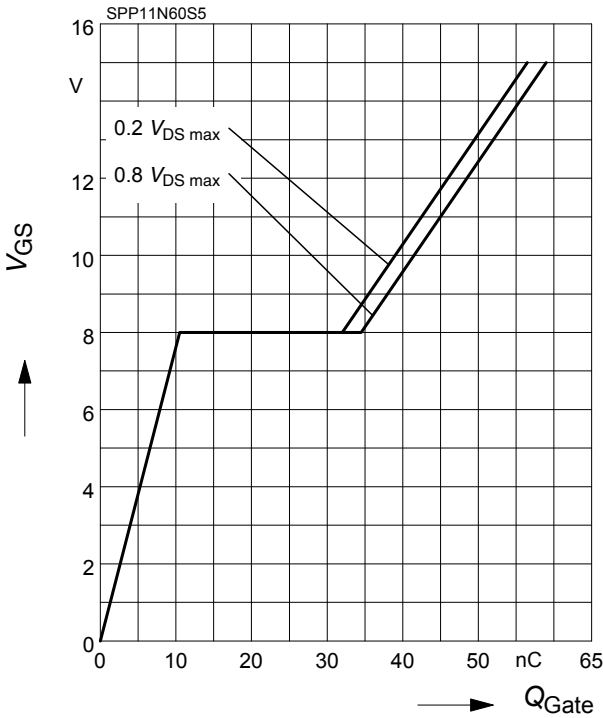
parameter: $t_p = 10 \mu\text{s}$



9 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

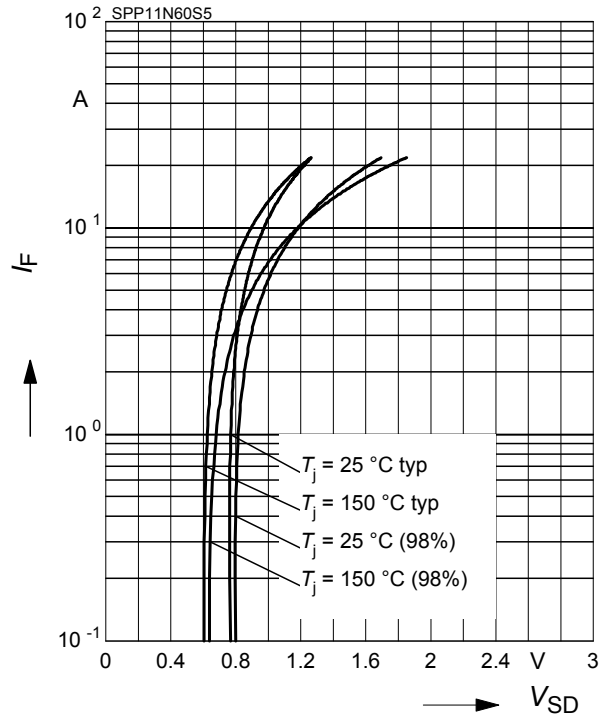
parameter: $I_D = 11\text{ A pulsed}$



10 Forward characteristics of body diode

$I_F = f(V_{SD})$

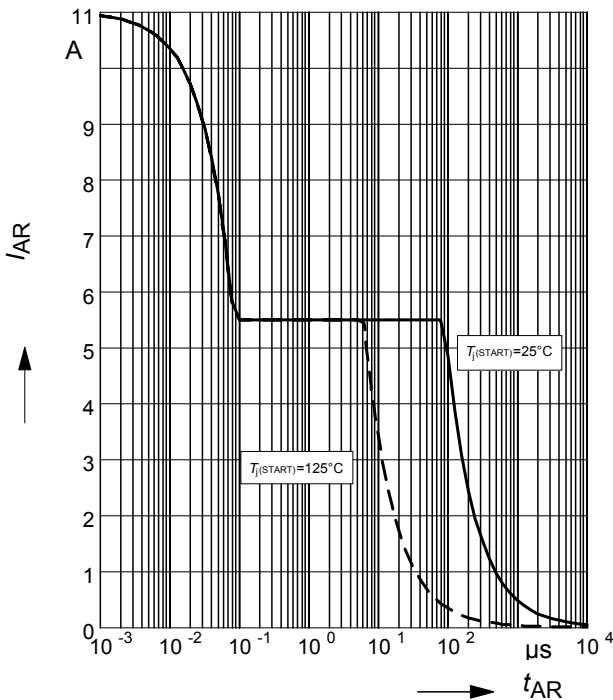
parameter: $T_j, t_p = 10\ \mu\text{s}$



11 Avalanche SOA

$I_{AR} = f(t_{AR})$

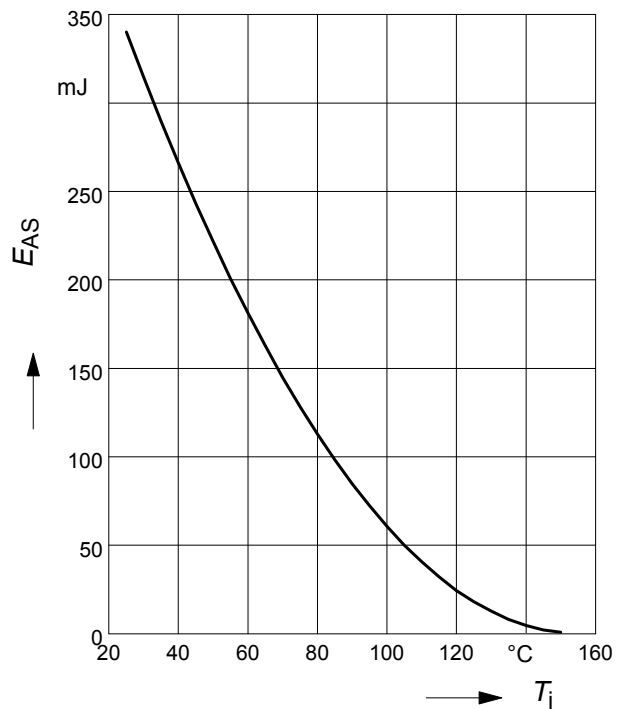
par.: $T_j \leq 150\ \text{°C}$



12 Avalanche energy

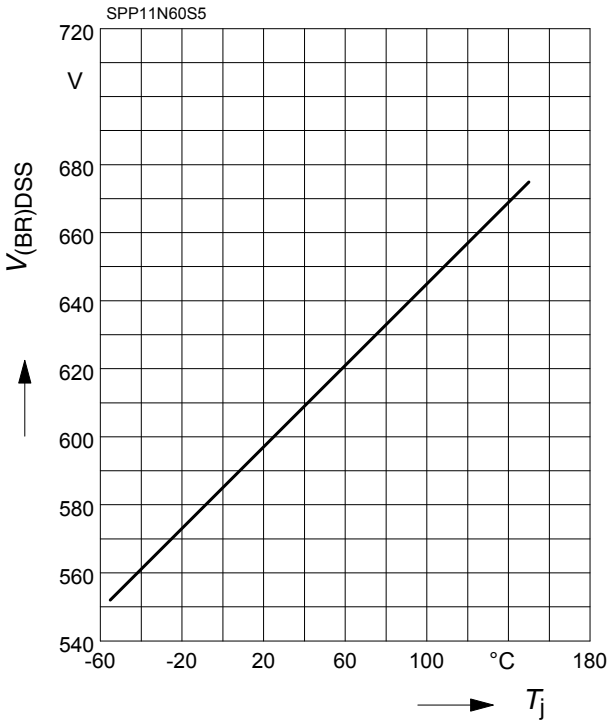
$E_{AS} = f(T_j)$

par.: $I_D = 5.5\text{ A}, V_{DD} = 50\text{ V}$



13 Drain-source breakdown voltage

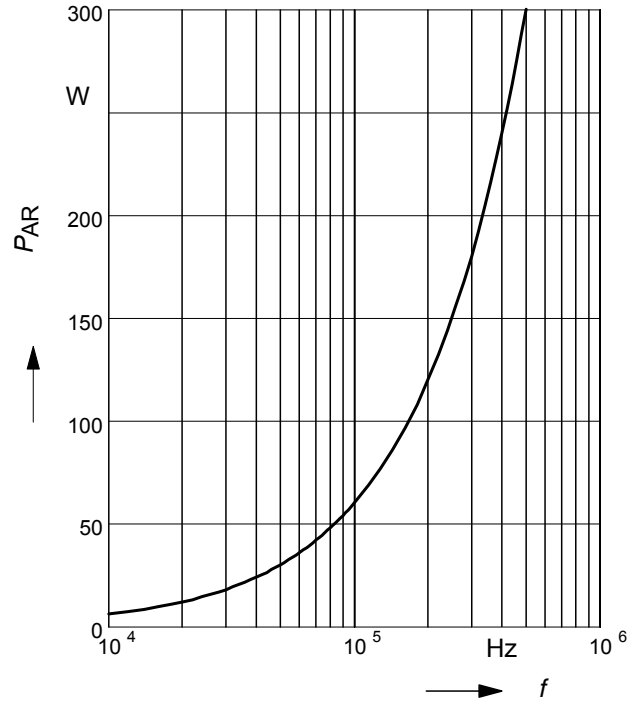
$$V_{(BR)DSS} = f(T_j)$$



14 Avalanche power losses

$$P_{AR} = f(f)$$

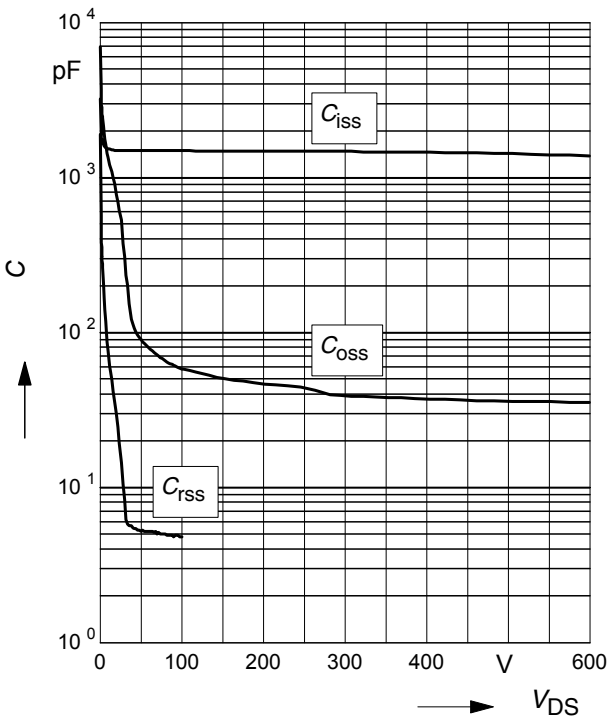
parameter: $E_{AR}=0.6mJ$



15 Typ. capacitances

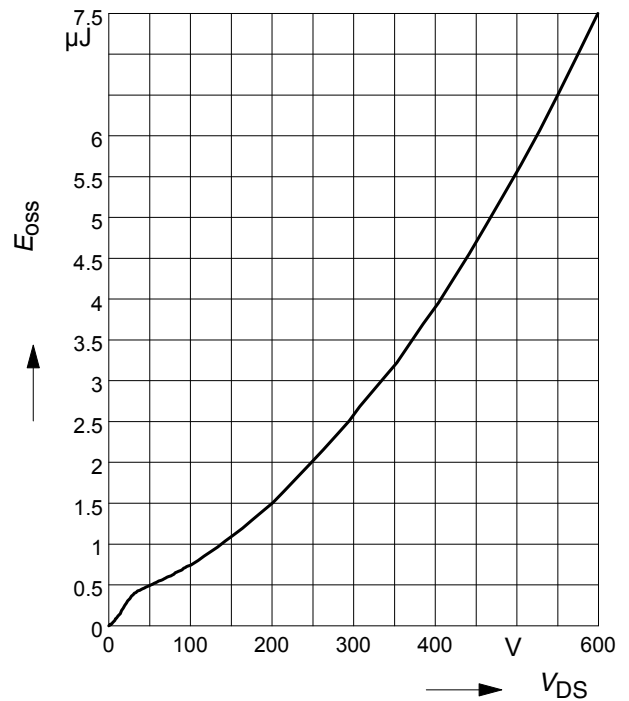
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1 MHz$

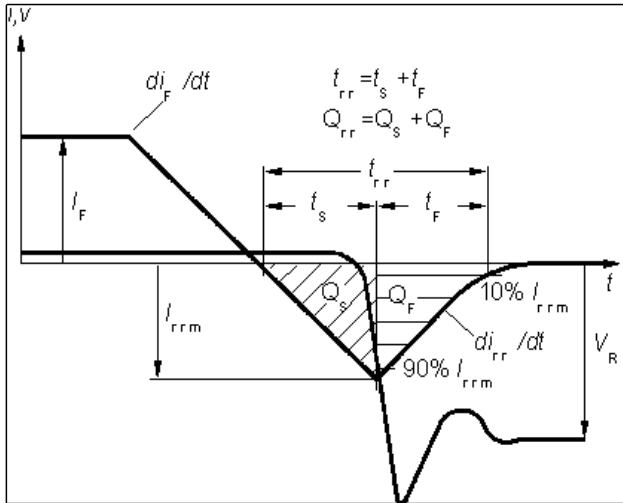


16 Typ. C_{OSS} stored energy

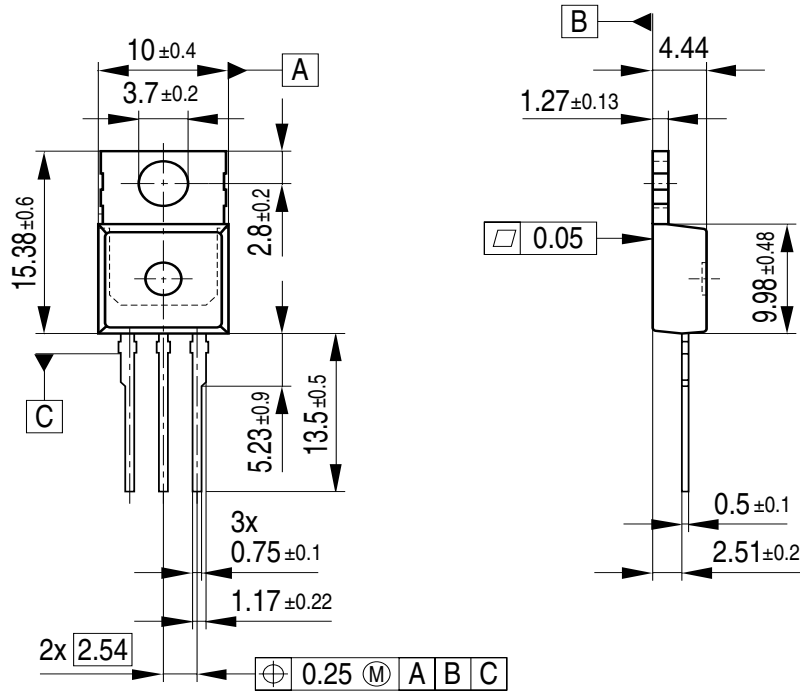
$$E_{Oss}=f(V_{DS})$$



Definition of diodes switching characteristics

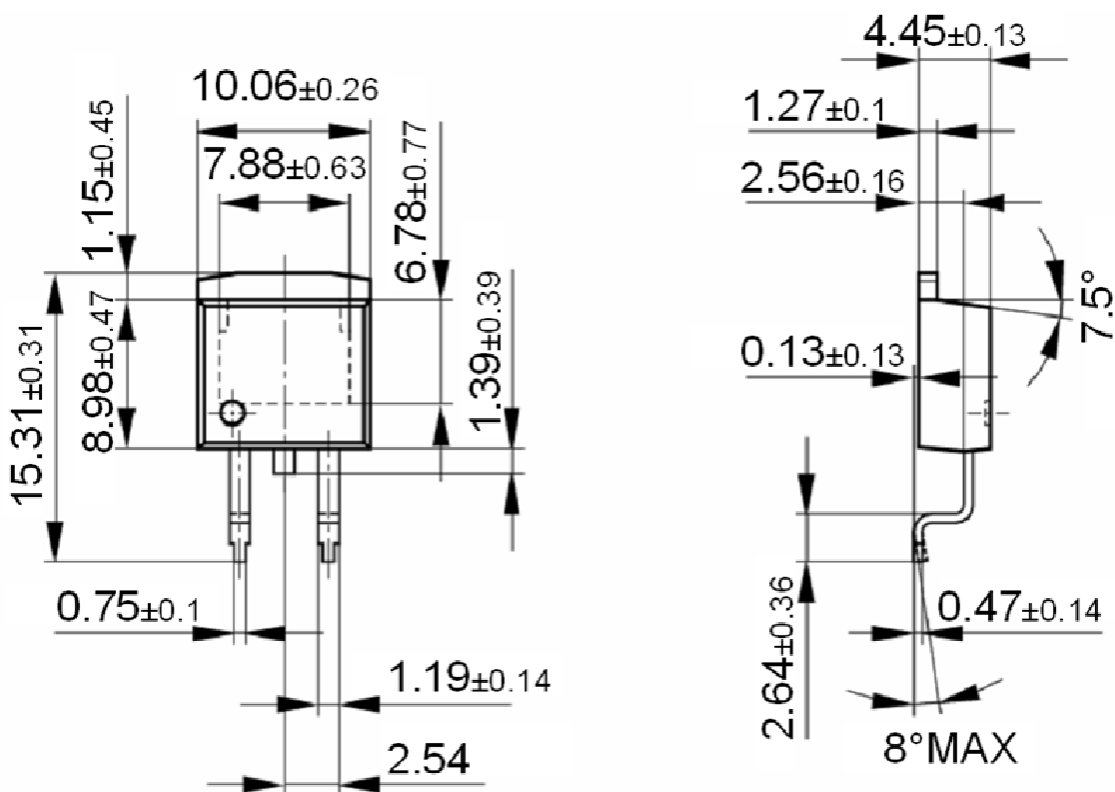


P-TO-220-3-1

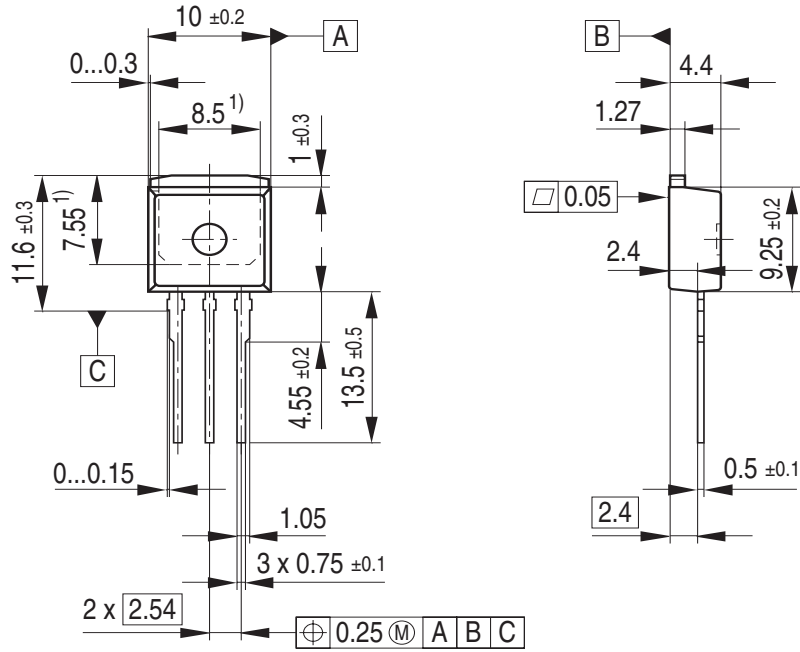


All metal surfaces tin plated, except area of cut.
Metal surface min. x=7.25, y=12.3

P-TO-263-3-2 (D²-PAK)



P-TO-262-3-1 (I²-PAK)



1) Typical

Metal surface min. X = 7.25, Y = 6.9

All metal surfaces tin plated, except area of cut.



SPP11N60S5, SPB11N60S5 SPI11N60S5

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